

Crownpo Technology

## **Product Profile**

### Feature

- 1. Meet IEC61000-4-2 (ESD) ±30kV (air), ±30kV (contact)
- 2. Meet IEC61000-4-4 (EFT) rating. 40A (5/50ns)
- 3. Meet IEC61000-4-5 (Lightning) rating. 10A (8/20 $\mu s$  )
- 4. Protects four two lines pairs
- 5. Low capacitance : 4.5pF @ 2.5V (Typical.)
- 6. Low leakage current : 10nA @ V\_{RWM}

#### Applications

- 1. 10/100/100M Ethernet ports
- 2. LAN/WLAN Equipment
- 3. Monitors and Flat Panel Displays
- 4. Telecom equipment, Ethernet port RJ45
- 5. Audi and Video equipment
- 6. Communication system

#### Mechanical Data

- 1. Case : DFN2010-8L small outline plastic package
- 2. Molding Compound Flammability Rating : UL 94V-O
- 3. High temperature soldering guaranteed: 260°C/10second
- 4. MSL1 and Thermally enhanced

#### **Pin Configuration**



#### **Ordering Information**

Package	Part Number	Packing	Marking
DFN2010-8L	ESDSR82V5BJ	3K pcs/7" Reel	2203

## **Mechanical Profile**

#### **Outline Drawing and Dimension**





Dimension	Unit (mm)		Unit (inch)		
	Min	Max	Min	Max	
А	0.370	0.430	0.015	0.017	
A1	0.000	0.050	0.000	0.002	
A2	0.130		0.005		
b	0.200	0.300	0.008	0.012	
D	1.900	2.100	0.075	0.083	
E	0.900	1.100	0.035	0.043	
е	0.500 typ.		0.020 typ.		
L	0.300	0.400	0.012	0.016	
R	0.050	0.150	0.002	0.006	

#### Maximum Ratings and Electrical Characteristics (Rating at 25°C ambient temperature unless otherwise specified) Maximum Ratings

Parameter		Symbol	Value	Unit
Peak Pulse Power	(tp=8/20µs waveform) (Note1.)	P <sub>PP</sub>	100	w
ESD per IEC 61000-4-2 (Note 2.)	(Air)	Vesd	±30	КV
ESD per IEC 61000-4-2	(Contact)		±30	C
Junction and Storage Temperature Range		TJ, TSTG	-55 ~ 150	C

#### **Electrical Characteristics**

Parameters		Symbols	Min	Мах	Units
Reverse Stand-Off Voltage		V <sub>RWM</sub>	-	2.50	V
Reverse Breakdown Voltage (Note 3.)	I <sub>t1</sub> =1µA	V <sub>t1</sub>	3.00	4.50	V
Reverse Breakdown Voltage (Note 3.)	I <sub>h1</sub> =1mA	Vh	3.00	4.00	V
Reverse Leakage Current	V <sub>R</sub> =2.5V	I <sub>R</sub>	10		nA
Olemaine Mathema	I <sub>PP</sub> =2A	Vc	-	5.00	V
Clamping voltage	I <sub>PP</sub> =10A		-	8.00	V
Junction Capacitance	V <sub>R</sub> =2.5V, f=1MHZ	CJ	4.5 (Тур.)		РF

Note 1. Device stressed with ten non-repetitive current pulses (8/20µs exponential decay waveform according to IEC 61000-4-5 and IEC 61643-321). Note 2. Device stressed with ten non-repetitive ESD pulses.

Note 3. Bi-directional TVS characteristic as diagram (1) in the page 2.



# ESDSR82V5BJ

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Diagram (1). Bi-directional TVS characteristic



## **Rating and Characteristic Curves**

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## **Application Information**

- 1. Designed for protection of high-speed interfaces.
- 2. With typical capacitance of 4.5pF only, ESDSR82V5BJ is designed to protect parasitic-sensitive systems against over-voltage and over-current transient events.
- Designed to protect sensitive components which are connected to data and transmission lines from overvoltage caused by electrostatic discharge (ESD), electrical fast transients (EFT), and lightning.
- 4. Each ESDSR82V5BJ device can protect two high-speed line pairs.
- 5. The "flow-thru" design minimizes trace inductance and reduces voltage overshoot associated with ESD events The
- 6. combined features of low capacitance and high ESD robustness makeESDSR82V5BJ ideal for high-speed data

port and high-frequency line (e.g., Gigabit Ethernet Ports) applications.

7. The low clamping voltage of the ESDSR82V5BJ guarantees a minimum stress on the protected IC.

## **Circuit Board Layout Recommendation**

Electronic equipment is susceptible to damage caused by a variety of sources, including Electrostatic Discharge (ESD), Electrical Fast Transients (EFT) and Lightning strikes.

The ESDSR82V5BJ was designed to protect to the sensitive equipment from damage which may be induced by such transient events.

This product can be configured in a connection to meet the requirement of differential line pairs as follows:



Schematic Diagram for Gigabit Ethernet ESD/Surge Protection